

Radiation hard SiPM development

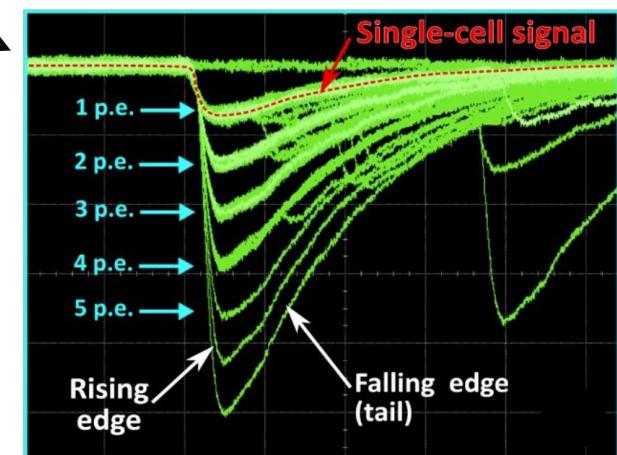
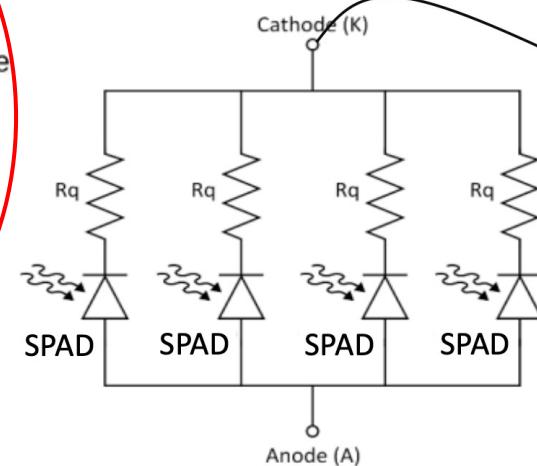
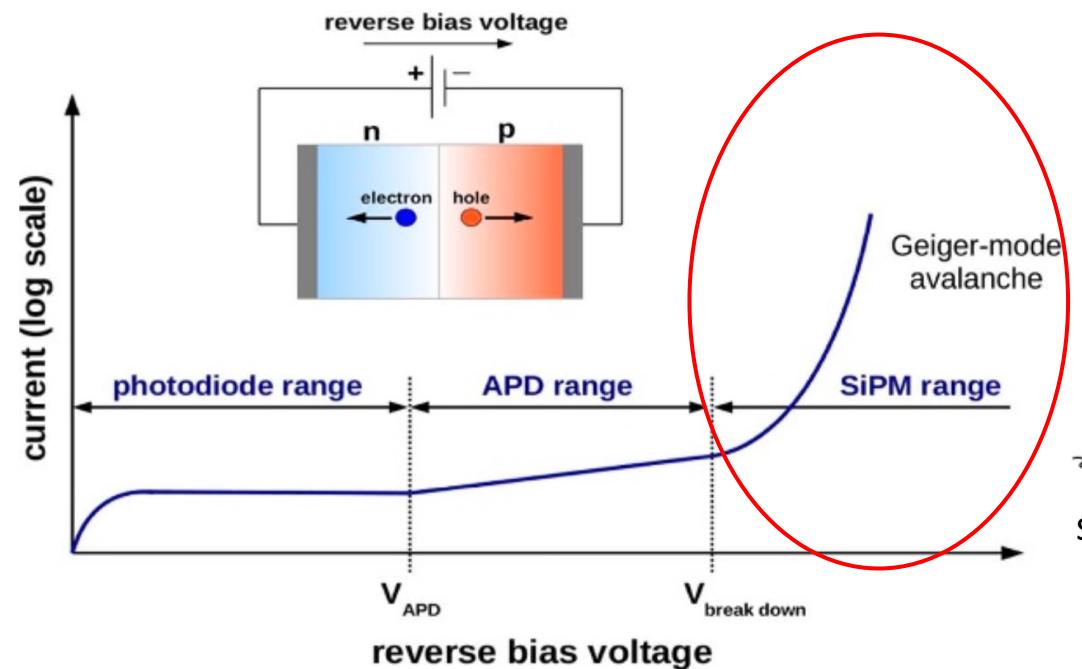
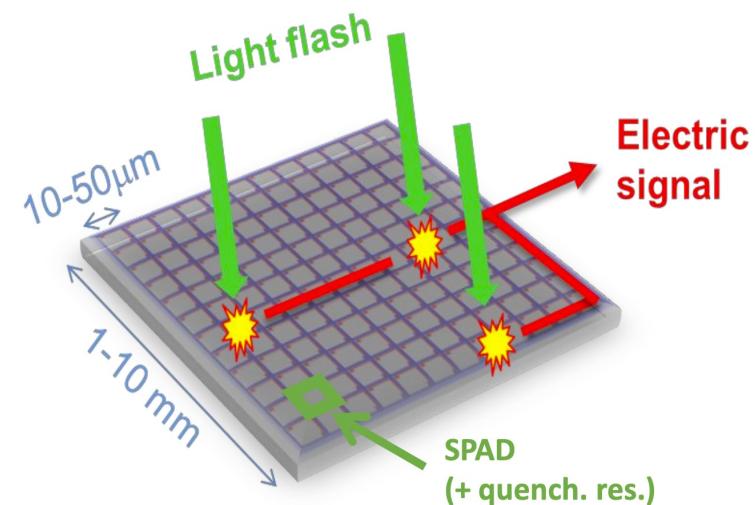
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梁志均

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SiPM introduction

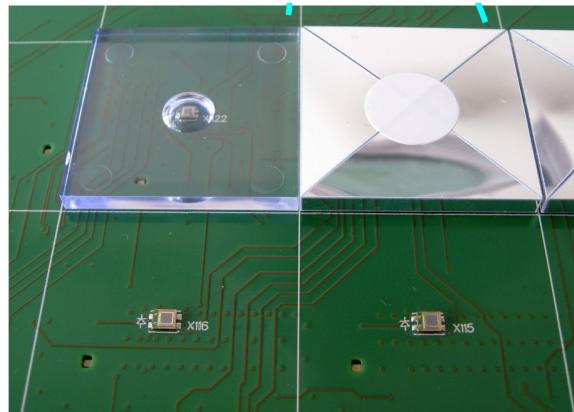
- SiPM--silicon photomultiplier: advantage:
 - High resolution
 - Single photon counting
- The goal is to develop Radiation hard SiPM



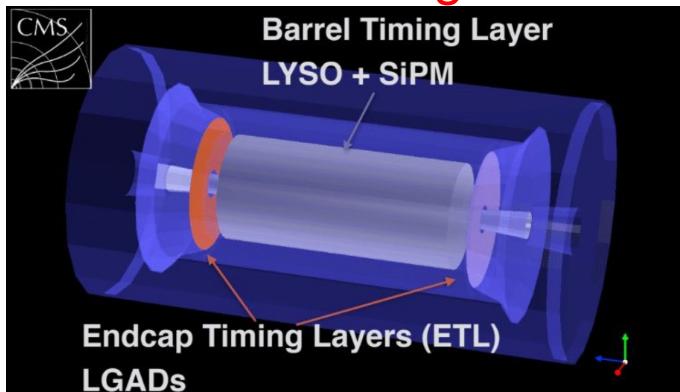
Radiation SiPM application

- Astrophysics: Space station scientific experiment (Herd ...)
- Collider physics: calorimeter application
 - CMS timing layer, calorimeter
 - CEPC calorimeter and time of flight detector

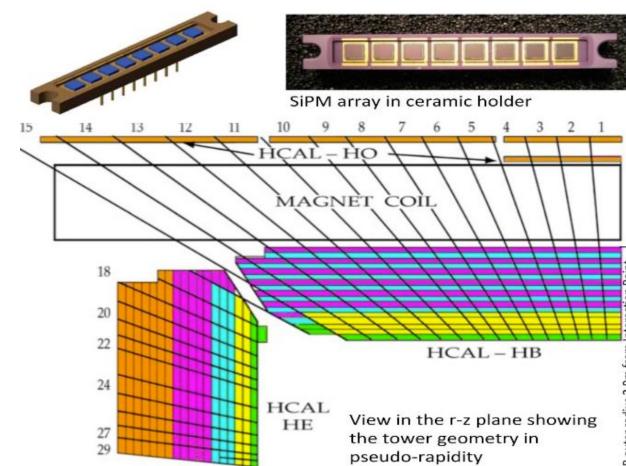
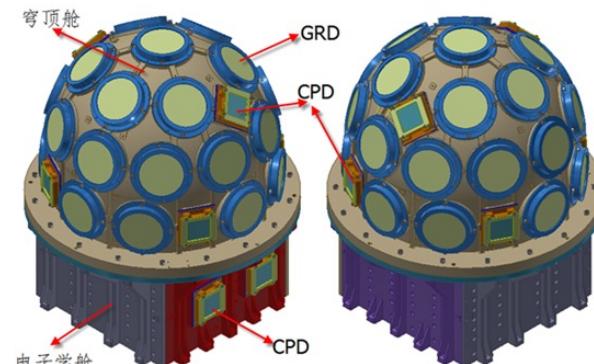
CEPC PFA
calorimeter
prototype



CMS MIP timing detector



GECAM



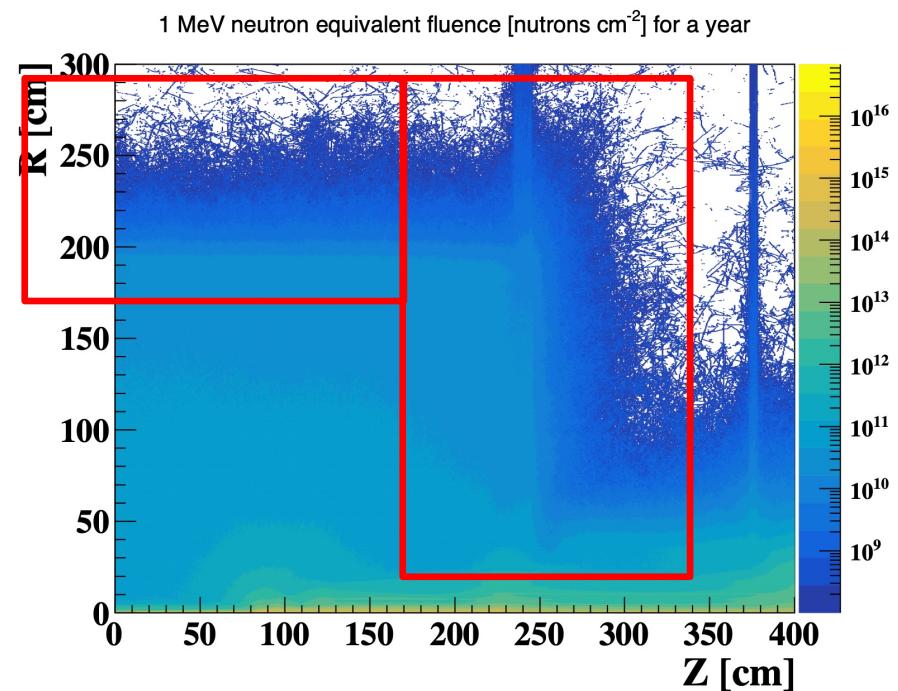
CMS Calorimeter

SiPM radiation hardness challenge

- After 10 year operation of CEPC, fluence is above $10^{13} \text{ n}_{\text{eq}}/\text{cm}^2$
- SiPM typically work below 1krad or $10^9 \text{ n}_{\text{eq}}/\text{cm}^2$ fluence
 - Performance drop after 1krad or $10^9 \text{ n}_{\text{eq}}/\text{cm}^2$
 - In great need to develop radiation hard SiPM

	Long term Satellite or Space station application	CEPC requirement
TID does	100 krad	>100 krad
Fluence	$\sim 10^{10} \text{ n}_{\text{eq}}/\text{cm}^2$	$>10^{13} \text{ n}_{\text{eq}}/\text{cm}^2$

Fluence in ZH run (240GeV)

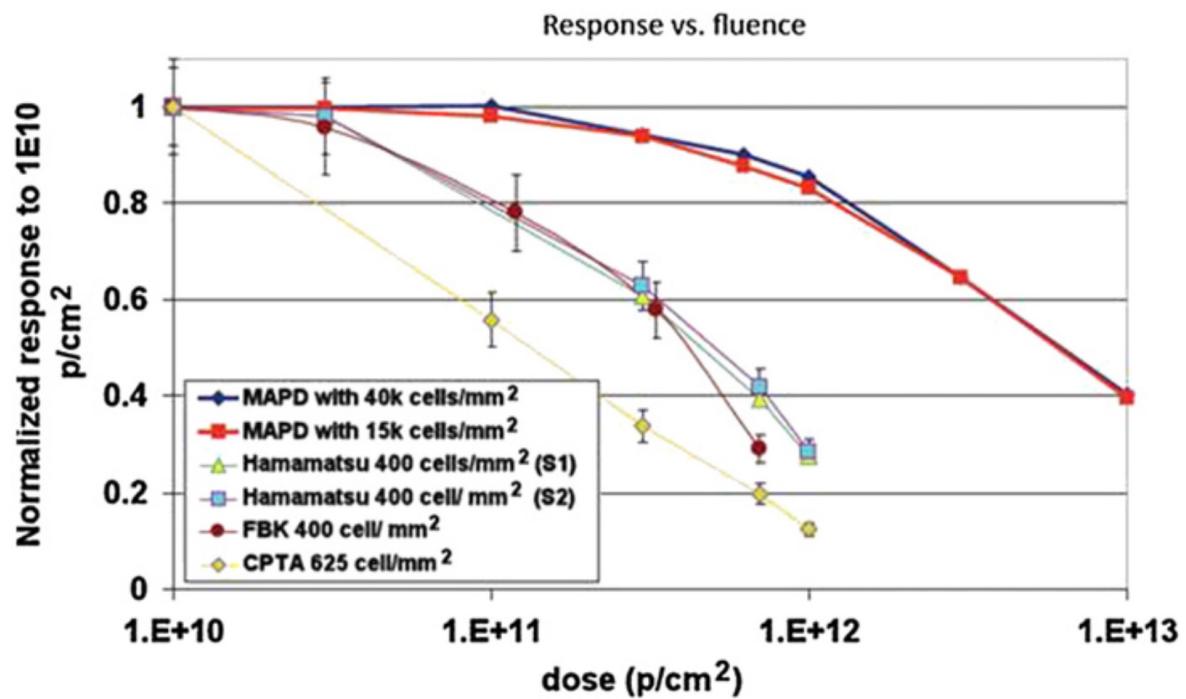


SiPM Radiation hardness

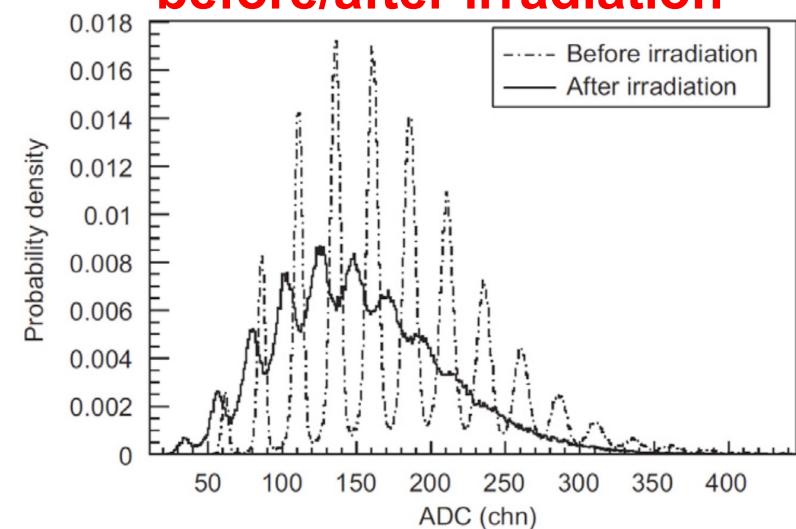
■ After $10^{10} \text{ n}_{\text{eq}}/\text{cm}^2$ or 10Krad dose

- Signal gain decrease
- Energy resolution decrease
- Dark count increase

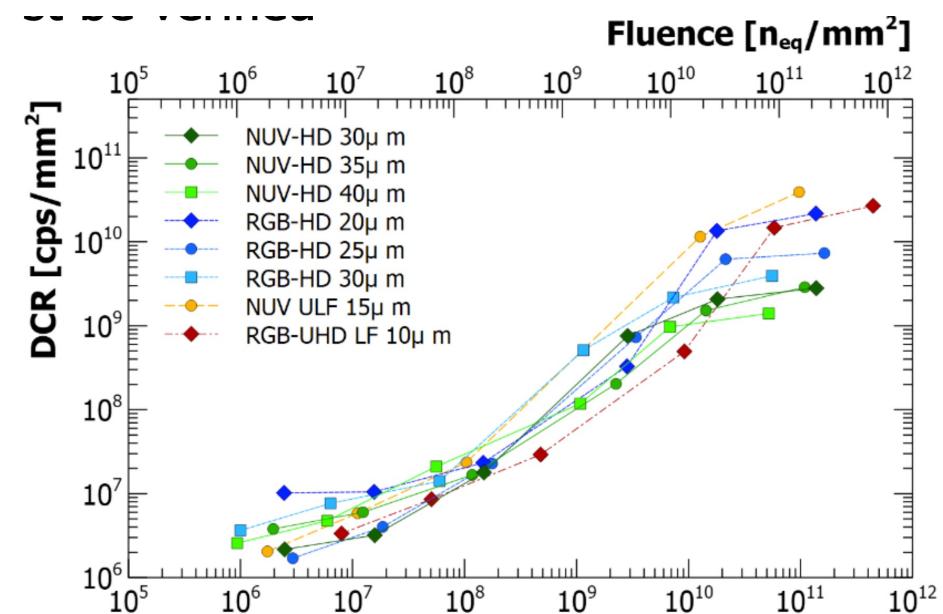
SiPM gain VS Dose



Energy resolution before/after irradiation

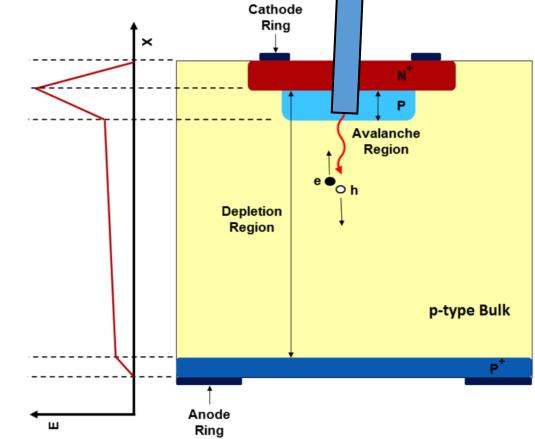
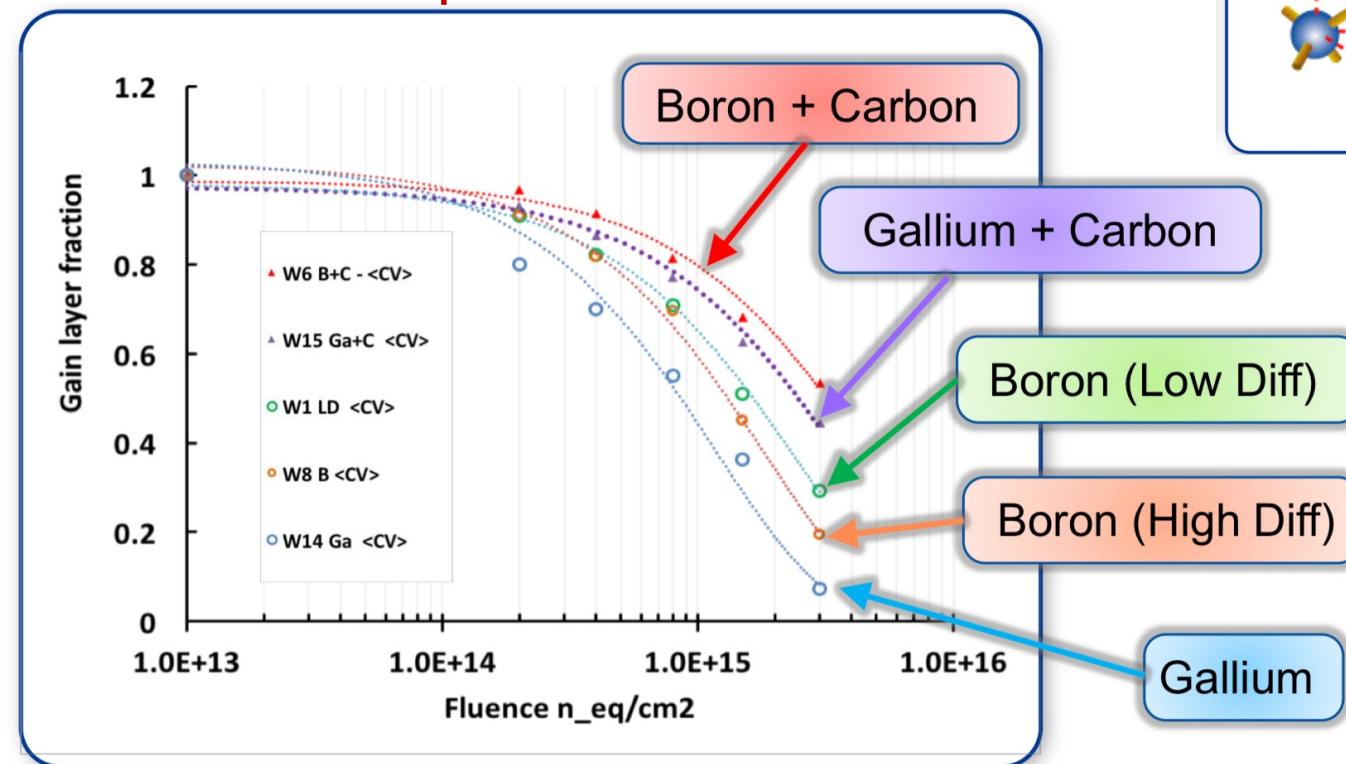
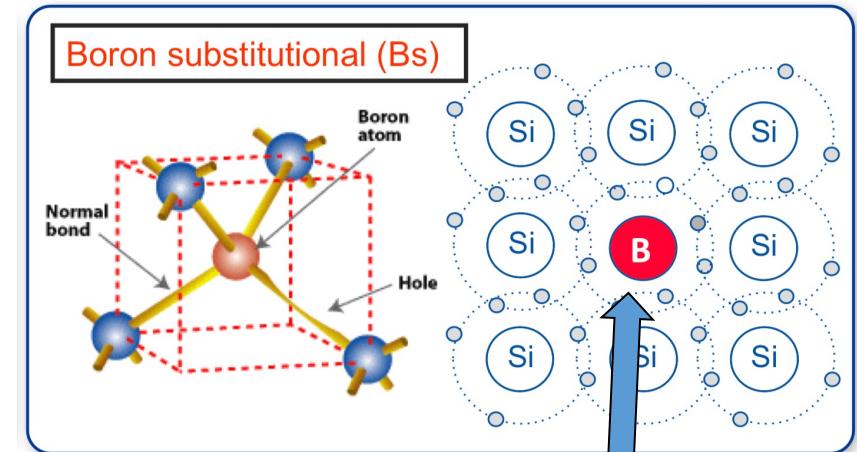
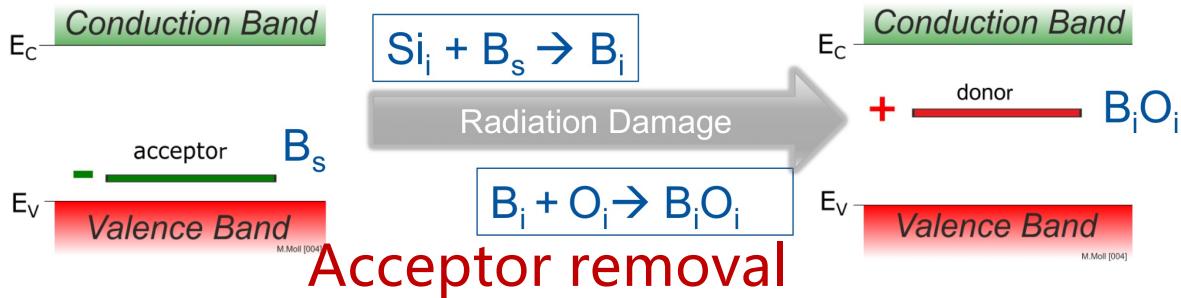


SiPM dark count VS Fluence



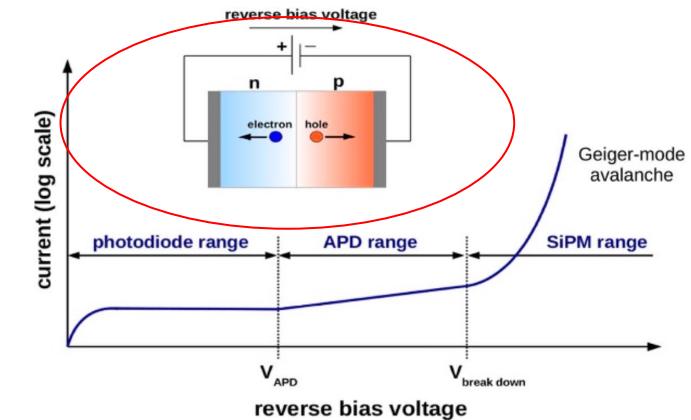
SiPM radiation hardness theory

- SiPM signal gain decreased after irradiation (p+ acceptor removal)

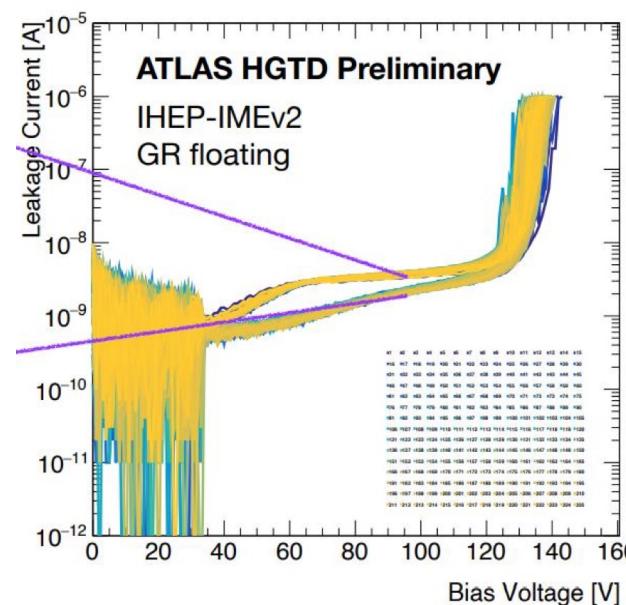
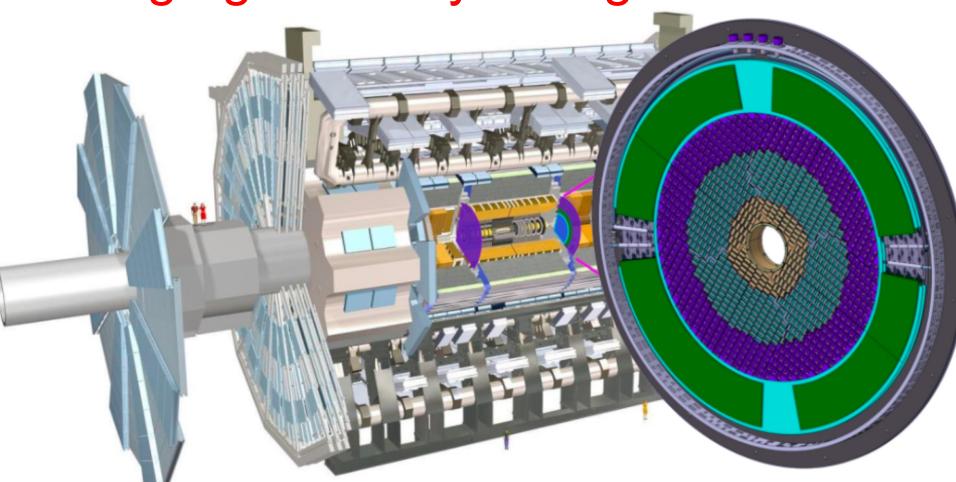


Radiation hard Low Gain Avalanche Detectors (LGAD)

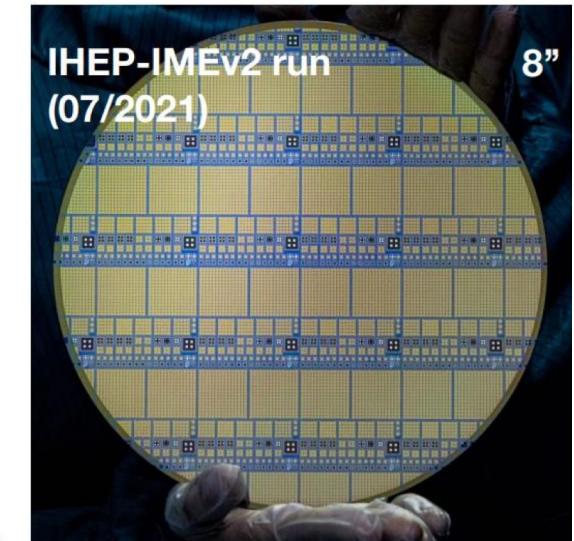
- IHEP developed radiation hard Low Gain Avalanche Detectors (LGAD)
- Developed for ATLAS high granularity timing detector
- LGAD and SiPM has similar structure
 - Good foundation for radiation hard SiPM development



LHC ATLAS experiment
High granularity timing detector

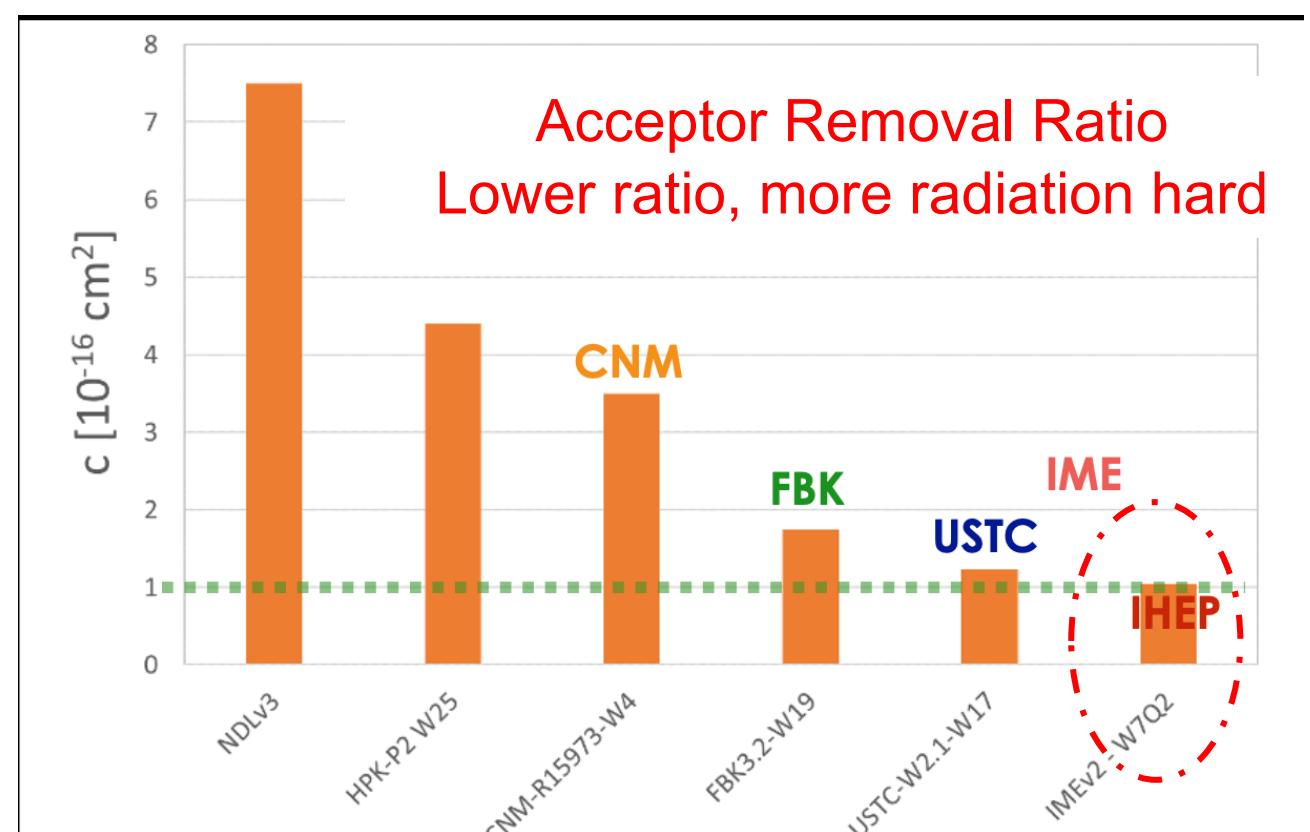
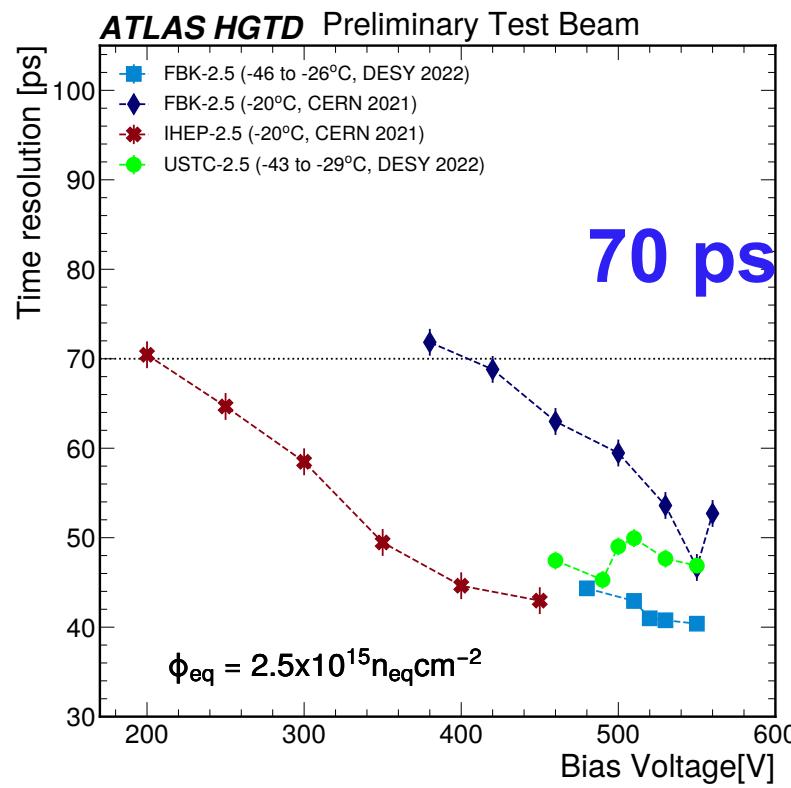


LGAD sensor developed by



LGAD sensor after Irradiation

- IHEP-IME LGAD with carbon-enriched doping
 - Significantly lower acceptor removal ratio, the most irradiation hard LGAD sensor by far
- After $2.5 \times 10^{15} n_{eq}/cm^2$, IHEP LGADs were operated at voltages below 350 V, avoid HV breakdown
 - Test beams at CERN and DESY, confirm the feasibility of LGAD timing detector for HL-LHC
 - IHEP made a leading contribution to radiation hard LGAD sensors



LGAD pre-production for ATLAS experiment

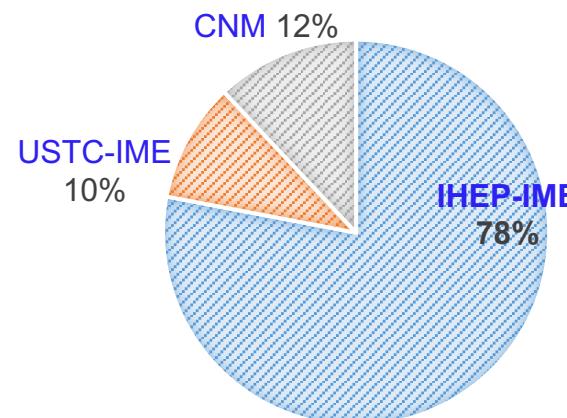
IHEP-IME sensor Won CERN tendering for ATLAS timing detector

- IHEP-IME: 78% (54% from CERN tendering+24% in-kind contribution)
- CNM: 12% in-kind contribution
- USTC-IME: 10% in-kind contribution

The first time that Chinese irradiation hard sensor used at LHC experiment

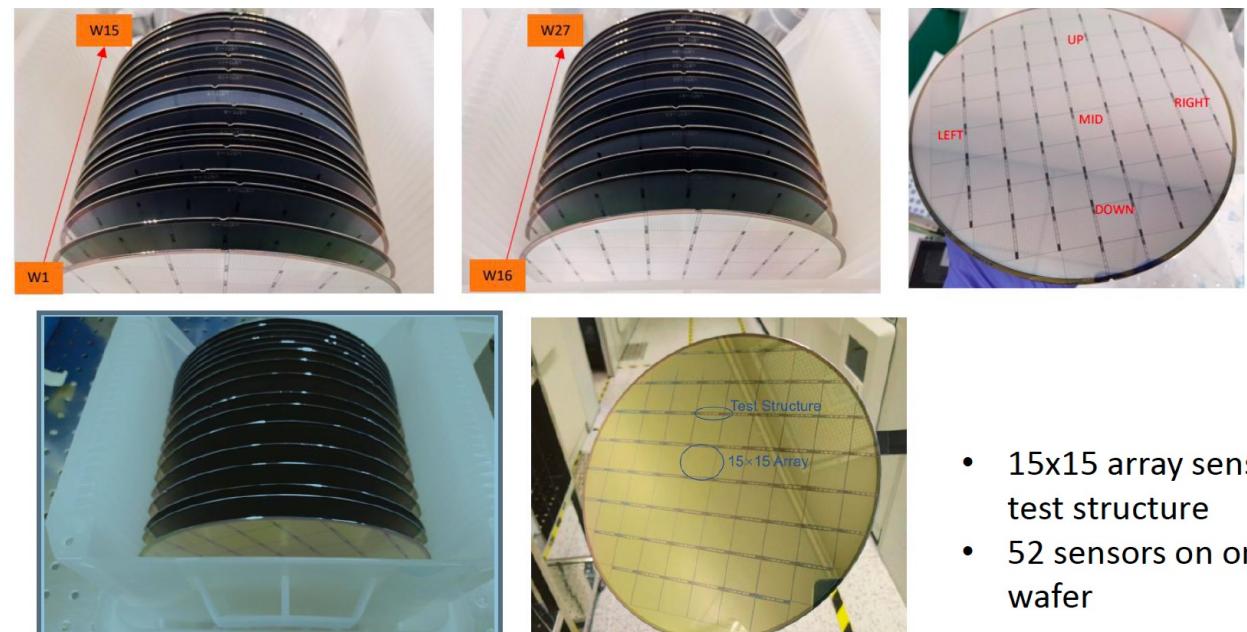
Pre-production LGAD sensors from China

Share of production between vendors



USTC-IME
Pre-production

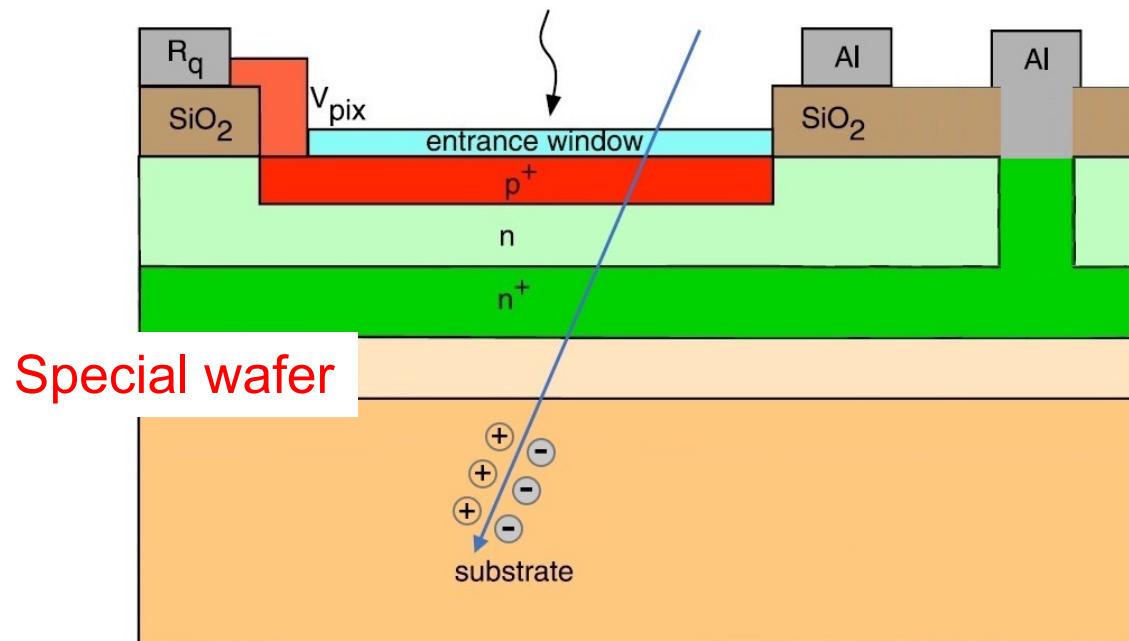
IHEP-IME
Pre-production



- 15x15 array sensors and test structure
- 52 sensors on one 8inch wafer

SiPM dark count after irradiation

- Bulk damage after irradiation → dark count increased
- Potential Solution:
 - Design a special wafer to isolate the dark current from bulk damage



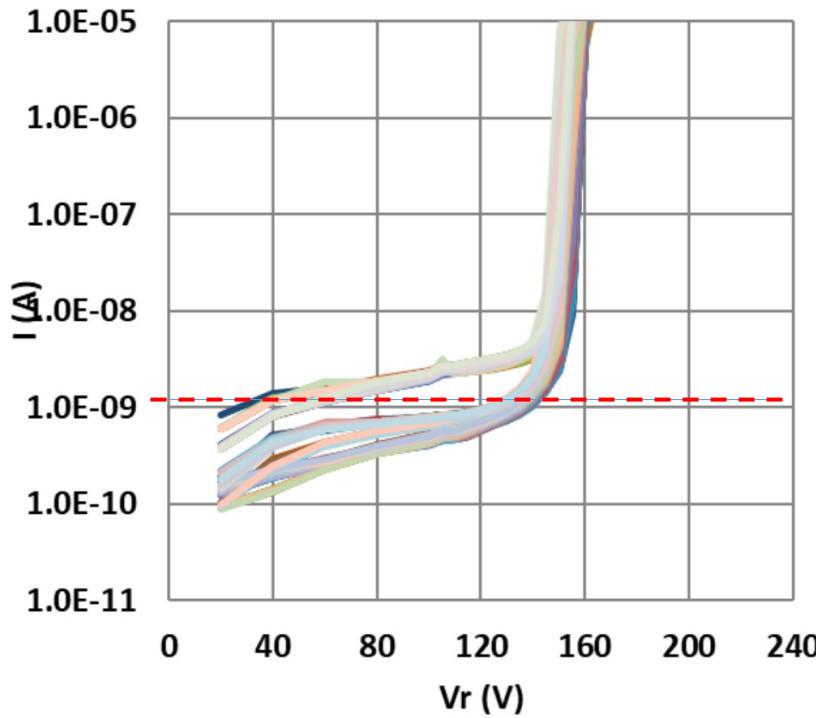
Leakage current of LGAD before irradiation

- First trial of this special wafer idea in LGAD development
 - The leakage current of IHEP LGAD is low before irradiation

Bias voltage Vs Dark current (HPK LGAD)

Dark current : $\sim 10^{-9} \text{ A}$

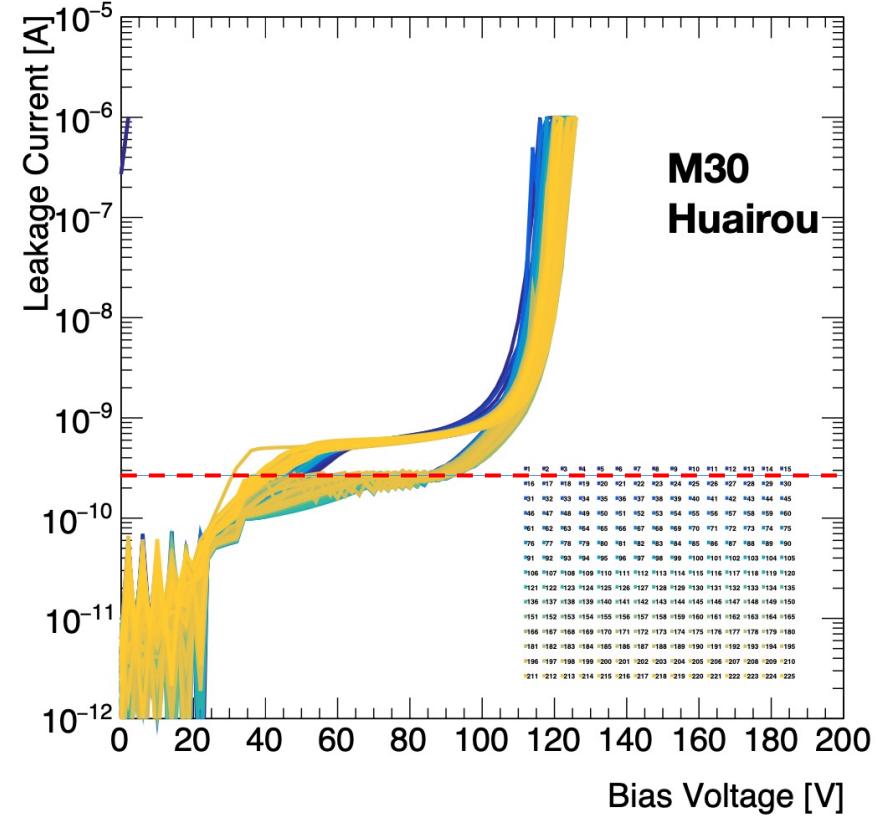
ATLAS 15x15-P3



Bias voltage Vs Dark current (IHEP LGAD)

Dark current : $\sim 2*10^{-10} \text{ A}$

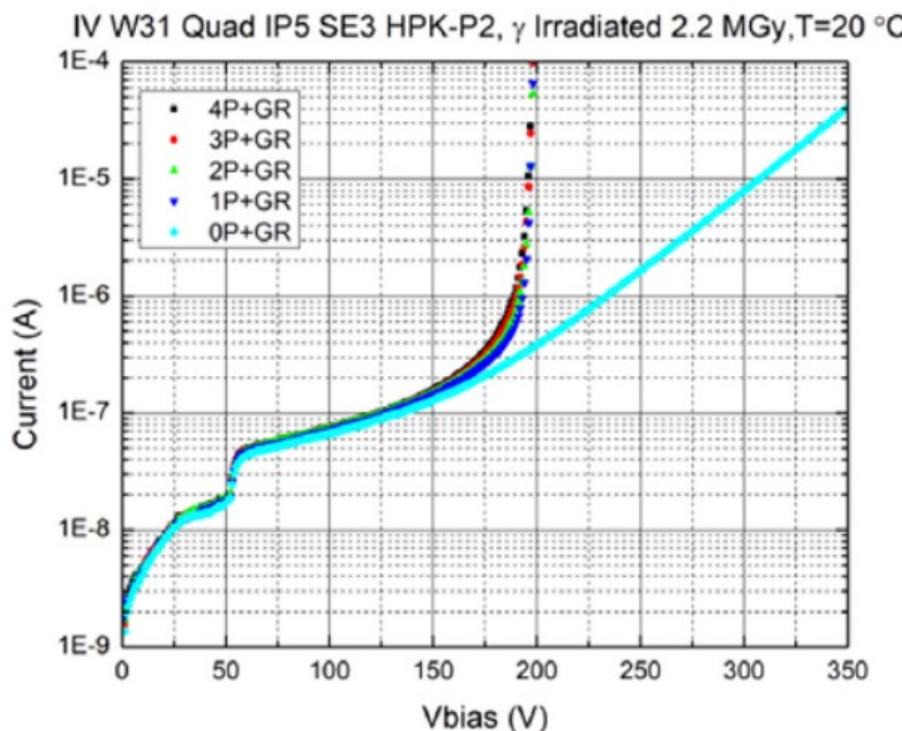
M30
Huairou



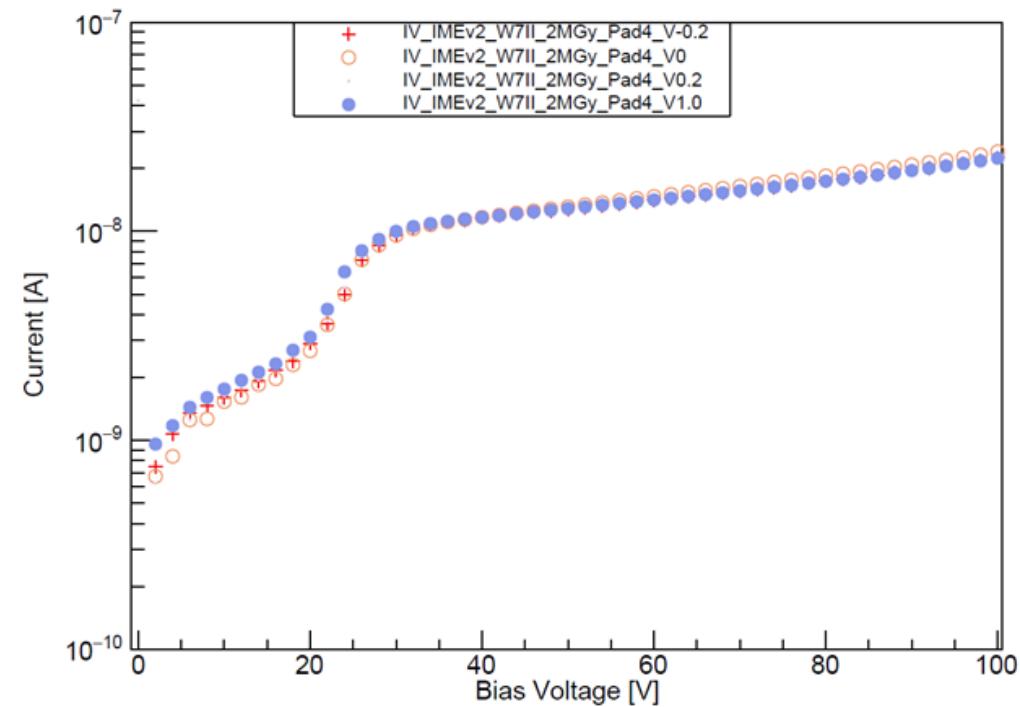
Leakage current of LGAD after irradiation

- After 200 MRad TID dose
 - IHEP LGAD showed a low leakage current
 - Validate the idea of special wafer

Bias voltage Vs Dark current (HPK LGAD)
Dark current : $\sim 10^{-7}$ A

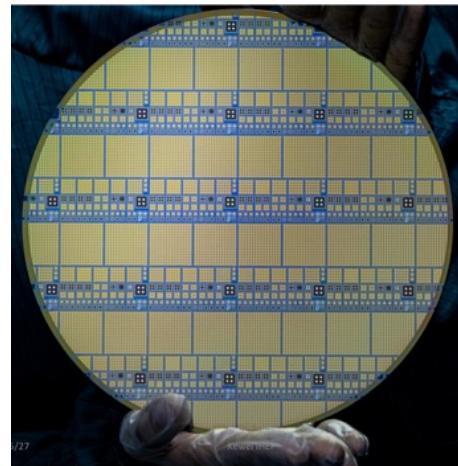


Bias voltage Vs Dark current (IHEP LGAD)
Dark current : $\sim 2 \times 10^{-8}$ A

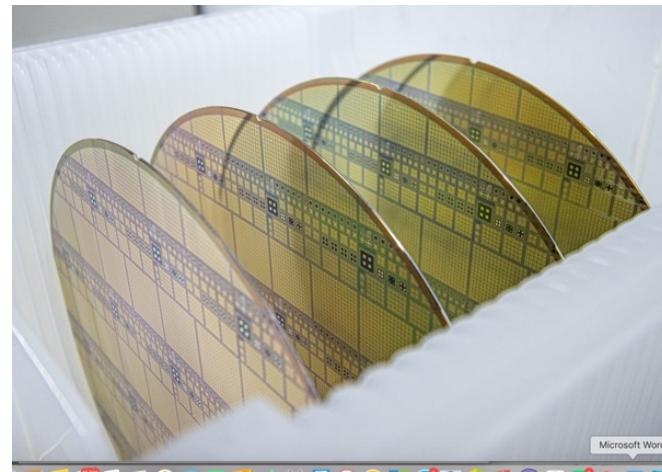


Time line for radiation hard SiPM

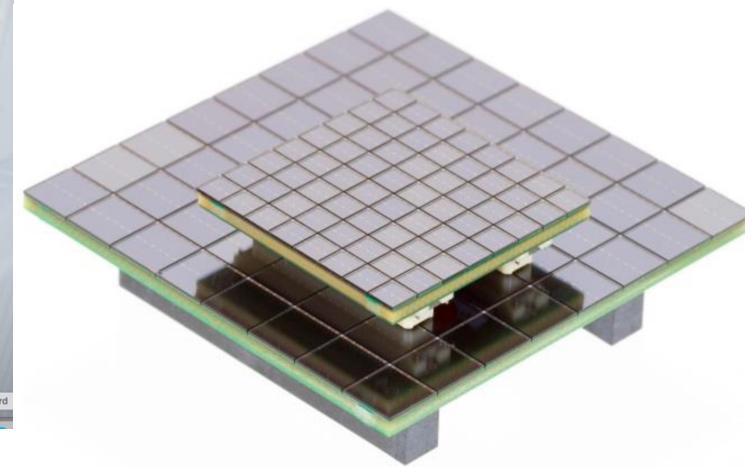
- 2023 1st half :SiPM irradiation hard design validated in LGAD engineering run
- 2023 2nd half : 1st Dedicated SiPM engineering run submission
- 2024: 1~2 more dedicated SiPM engineering run
- 2025: built modules or working device based on radiation hard SiPM



仿真与探索各种工艺参数



SiPM的多次流片，确定工艺参数



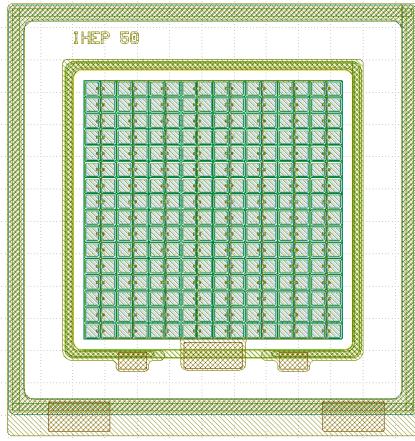
2023

2024

2025

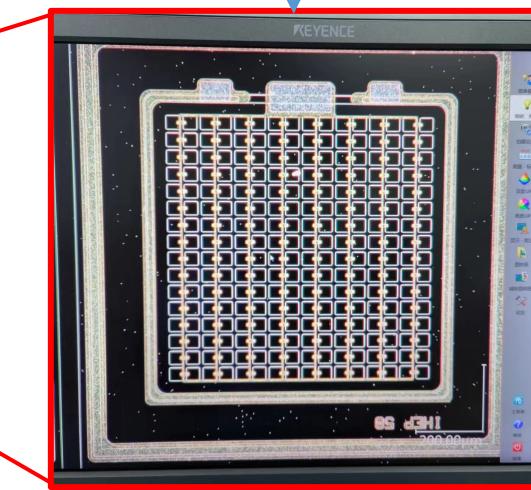
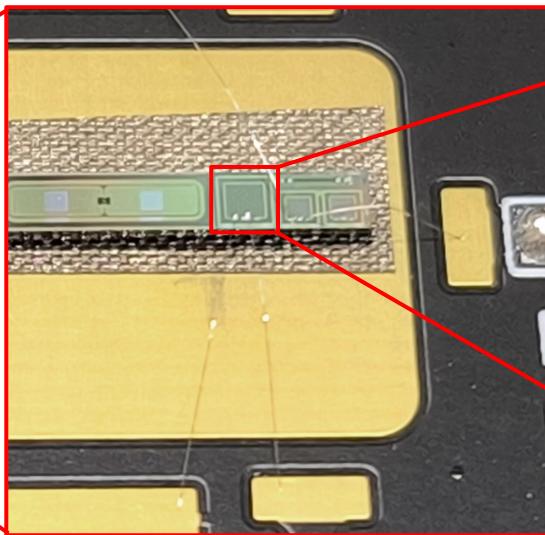
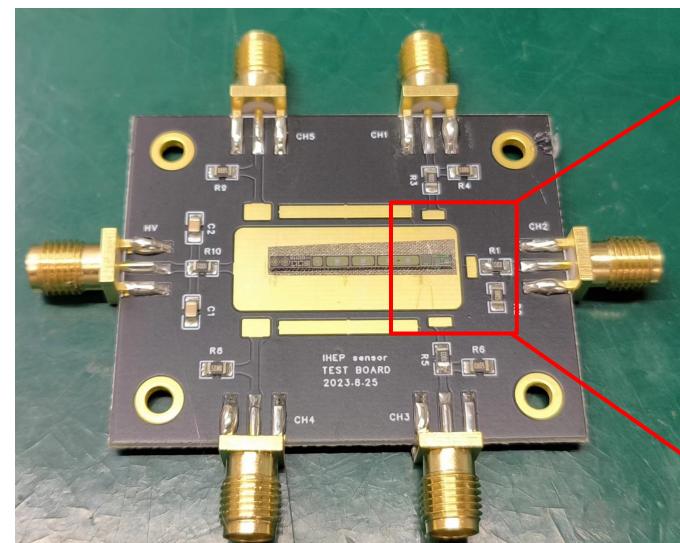
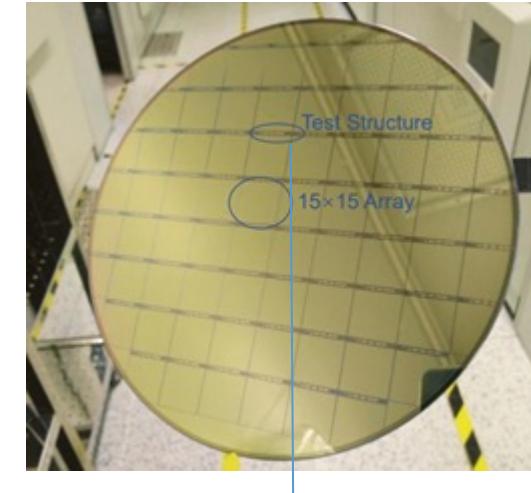
SiPM sample from 1st trial MPW run

- We put a small SiPM design on LGAD prod

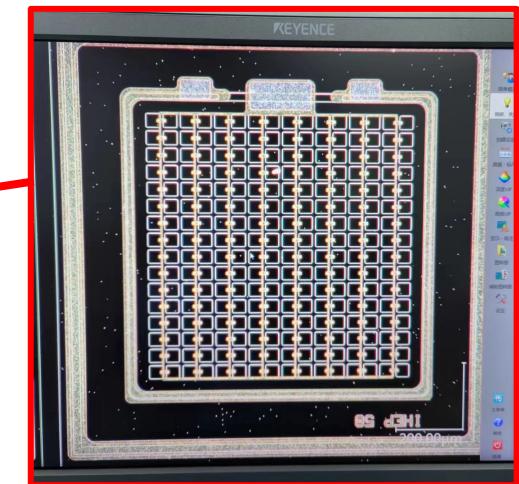
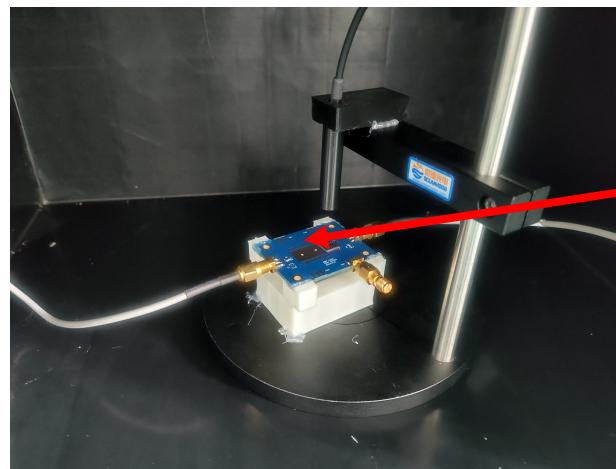
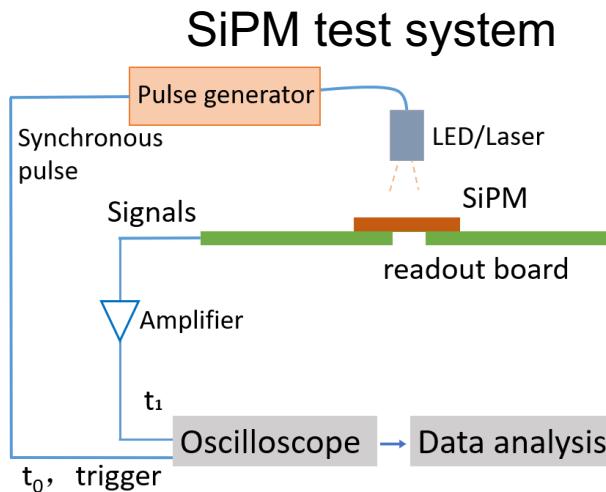


- Pixel size : 50μm
- 16 x 16 pixels

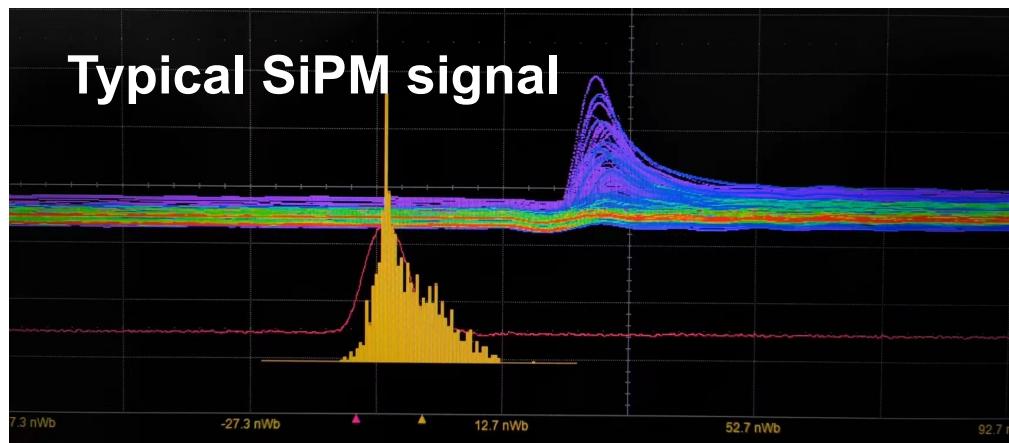
SiPM



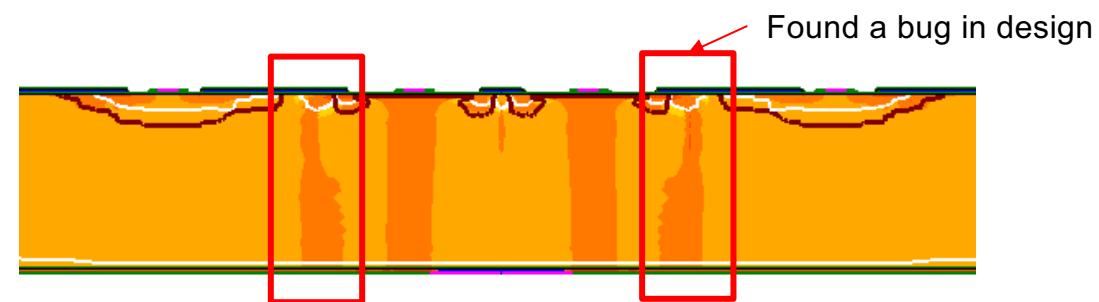
SiPM sample from 1st trial MPW run



Typical SiPM signal



SiPM layout and process has been validated



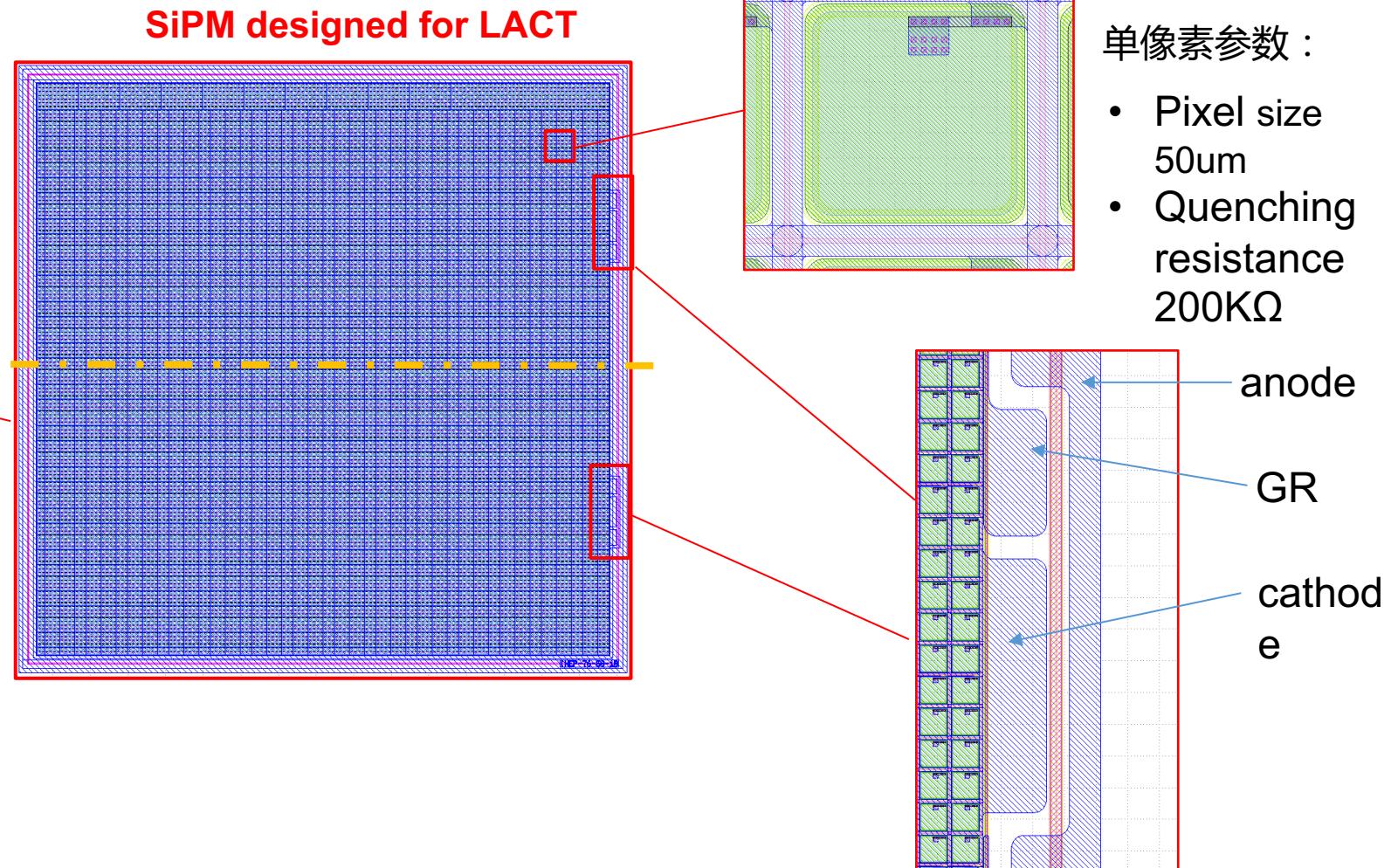
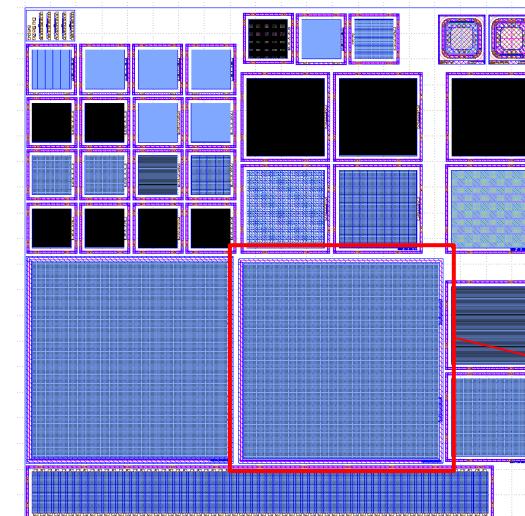
SiPM Leakage current is a bit high in 1st trial run

- Pstop and GR design has some issue
- Optimized the design for engineering runs

Dedicated SiPM engineering run

- Dedicated radiation hard SiPM run will be submitted next month

- Various SiPM size: 1*1mm, 3*3mm, 5*5mm
- Various Pixel size: 10um ,20um, 50um



Summary

- Development for radiation hard SiPM
 - Aim for CEPC and Astrophysics application
- Key technology has been validated in ATLAS HGTD detector project
 - Radiation hard LGAD sensor developed by IHEP team
 - First domestic Radiation hard silicon sensor used in LHC experiment
- Radiation SiPM R & D project
 - 1st trial run has been submitted, and preliminary result obtained
 - Dedicated engineering run by the end of this year

谢谢！

研究方案：测试方案

■ 辐照测试方案：

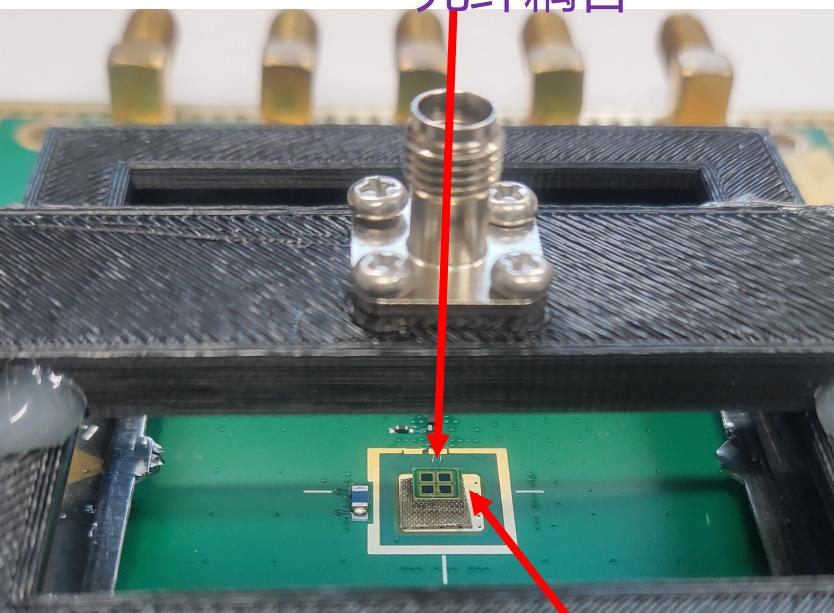
- 计划与东莞散裂团队合作，做SiPM的质子辐照

■ SiPM性能测试方案：

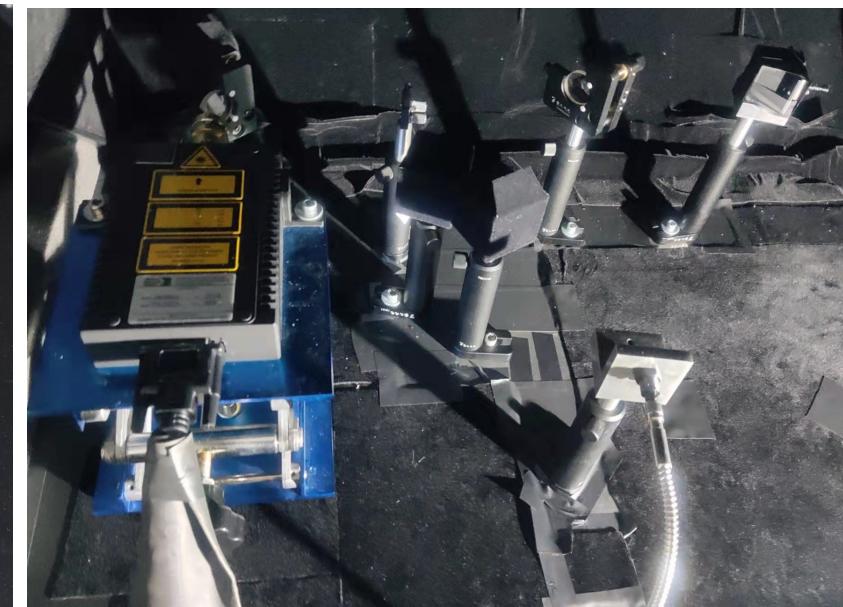
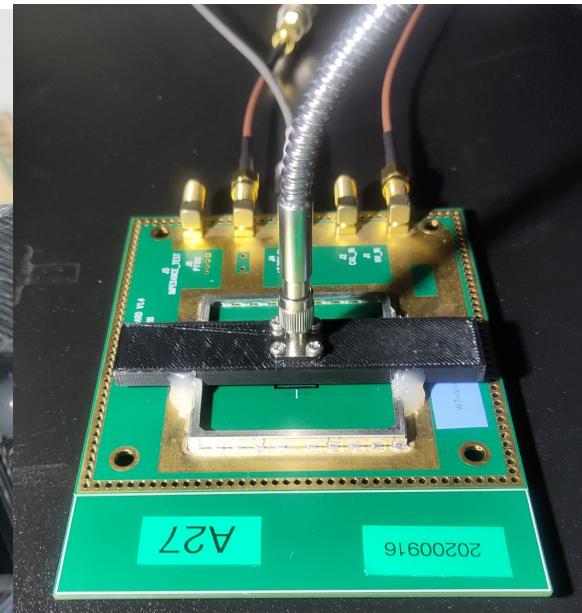
- 已有单光子测试平台与低温测试平台

目前基于LGAD传感器的弱光测试

光纤耦合



单光子测试平台（基于皮秒激光器）

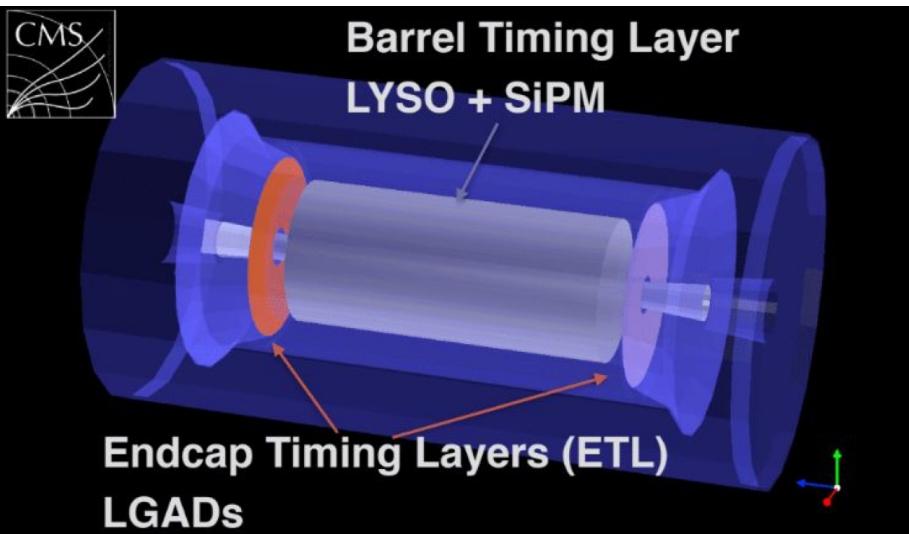


LGAD传感器

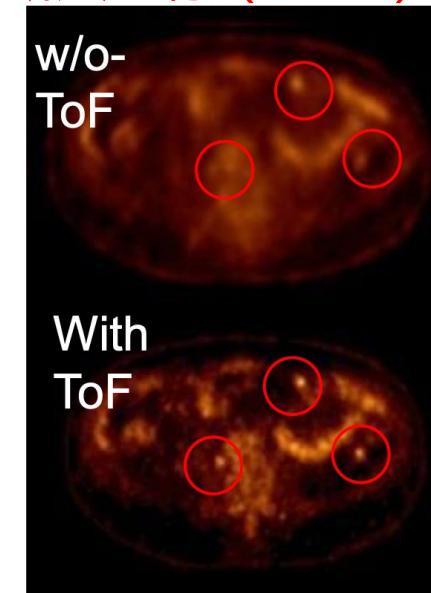
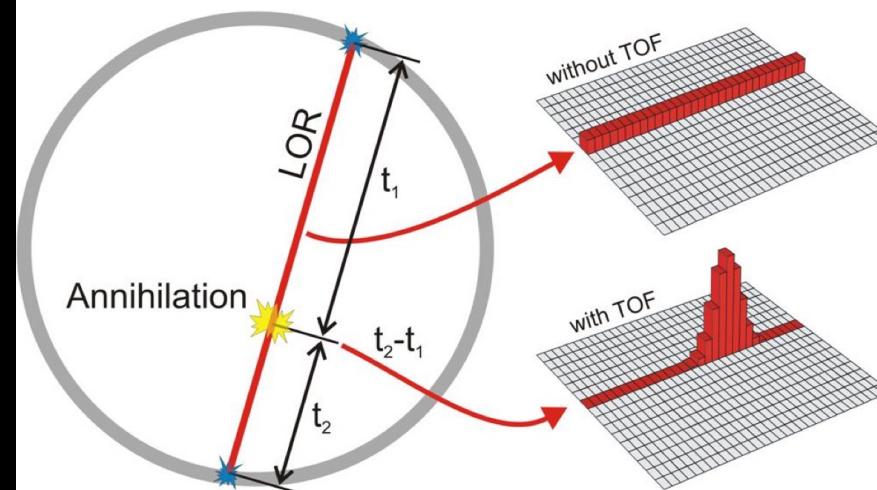
SiPM在时间测量上的应用

- 部分国外的SiPM有~30皮秒的本征时间分辨
- 未来有望用于各种时间探测器的应用中
 - 医学成像 (TOF-PET)，生物细胞成像
 - 飞行时间探测器

CMS的桶部时间探测器



超快SiPM在正电子发射型计算机断层显像 (PET)



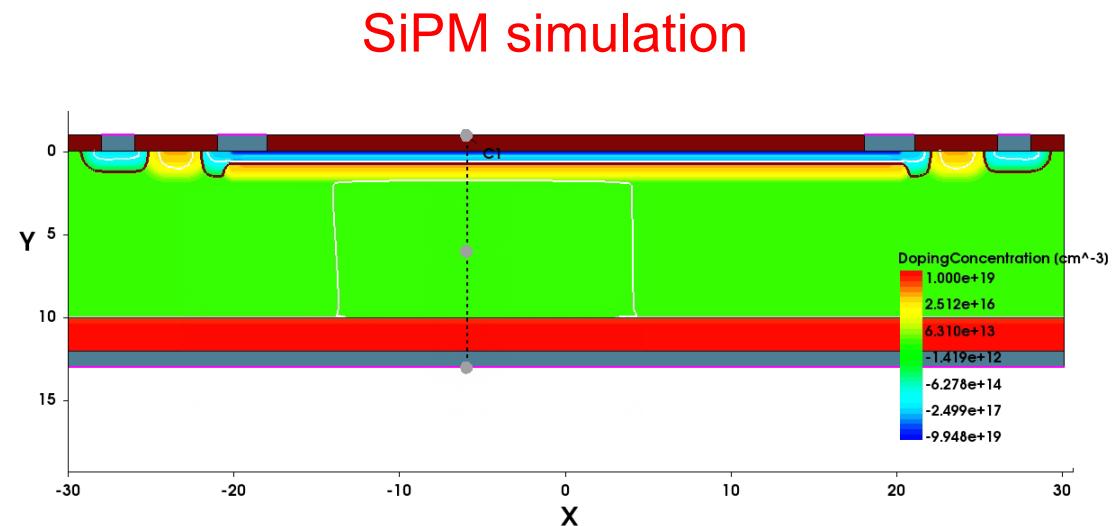
国内外形势：SiPM的暗计数

- 日本滨松与Sensi公司的SiPM是国际上领先的
- 国内以北师大的 SiPM 为代表
 - 在小像素SiPM的量子效率上很有特点
 - 在暗噪声水平与工艺一致性方面（量产能力），与国际水平有差距

	日本滨松SiPM	Sensi SiPM	北师大NDL SiPM
面积	3.0*3.0 mm ²	3.0*3.0 mm ²	3.0*3.0 mm ²
常温的暗计数 (kcps)	2000	860	~6000
Pitch	10 μm	28 μm	10 μm
Micro-cell Number	90000	10998	90000
Peak PDE	10%@470nm	24%@420nm	31%@420nm

1st MPW runs for radiation hard

- 完成第一版的工艺流程设计、TCAD仿真与版图设计



初步版图设计

- 器件面积：1 mm×1mm , 3 mm×3mm
- 像素尺寸：
 - 10 μm , 15 μm , 30 μm , 50um

